

TN22

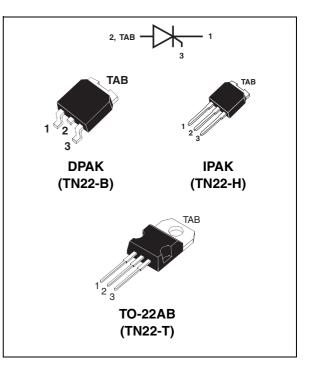
STARTLIGHT

FEATURES AND BENEFITS

- High clamping voltage structure (1200 -1500V)
- Low gate triggering current for direct drive from line (< 1.5mA)
- High holding current (> 175mA), ensuring high striking energy.

DESCRIPTION

The TN22 has been specifically developed for use in electronic starter circuits. Use in conjunction with a sensitive SCR and a resistor, it provides high energy striking characteristics with low triggering power. Thanks to its electronic concept, this TN22 based starter offers high reliability levels and extended life time of the fluorescent tubelamps.



Symbol	Parameter		Value	Unit
V _{RRM}	Repetitive peak off-state voltageTj = 110°C		400	V
I _{T(RMS)}	RMS on-state current Full sine ware (180° conduction angle)	Tc = 95°C	2	А
I _{T(AV)}	Mean on-state current $Tc = 95^{\circ}C$ Full sinewave (180° conduction angle)Tc = 95°C		1.8	А
	Non repetitive surge peak on-state current	tp = 8.3ms	22	Α
I TSM	(Tj initial = 25°C)	tp = 10ms	20	
2 I t	I ² t Value for fusing tp = 10ms		2	A ² s
dl/dt	Critical rate of rise of on-state current50 $I_G = 5mA dI_G / dt = 70 mA/\mu s.$ 50			A/µs
T _{stg} T _j	Storage and operating junction temperature range-40 to +150 -40 to +110			°C
ТІ	Maximum lead temperature for soldering during 10s at 4.5mm from case260			°C

Table 1: Absolute ratings (limiting values)

TN22

Table 2: Thermal resistance

Symbol	Parameter		Value	Unit
D	Junction to AMRIENIT	DPAK / IPAK	100	°C/W
nth(j-a)	R _{th(j-a)} Junction to AMBIENT	TO-220AB	60	0/10
R _{th(j-c)}	Junction to case		3	°C/W

GATE CHARACTERISTICS (maximum values)

 $P_{G (AV)} = 300 \text{ mW}$ $P_{GM} = 2W(t_p = 20 \text{ }\mu\text{s})$ $I_{FGM} = 1 \text{ A} (t_p = 20 \text{ }\mu\text{s})$ $V_{RGM} = 6V$

Table 3: Static electrical characteristics	(per diode)
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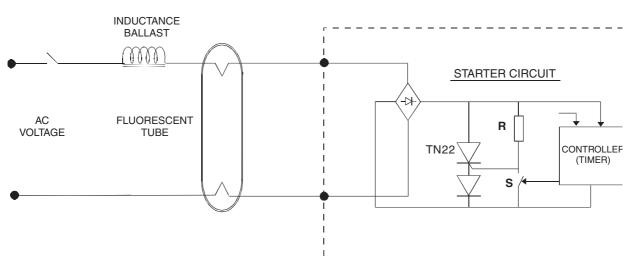
Symbol	Test conditions		Туре	Value	Unit
I _{GT}	V_D =12V (DC) R _L = 33 Ω	$T_j = 25^{\circ}C$	MAX	1.5	mA
V _{GT}	$V_D=12V (DC) R_L=33\Omega$ $R_{GK}=1 K\Omega$	$T_j = 25^{\circ}C$	MAX	3	V
Ι _Η	V _{GK} = 0V	$T_j = 25^{\circ}C$	MIN	175	mA
V _{TM}	$I_{TM} = 2A$ $t_p = 380 \mu s$	$T_j = 25^{\circ}C$	MAX	3.1	V
I _{DRM}	V _{DRM} Rated	$T_j = 25^{\circ}C$	MAX	0.1	mA
dV/dt	Linear slope up to V _D =67%V _{DRM} V _{GK} = 0V	T _j = 110°C	MIN	500	V/µs

Symbol	Symbol Test conditions 1		Value	Unit	
Symbol		Туре	TN22-1500	Onit	
$V_{\rm L} = 5m\Lambda V_{\rm L} = 0V_{\rm L} = 25^{\circ}$		MIN	1200	V	
V BR	V_{BR} $I_D = 5mA$ $V_{GK} = 0V$ $T_j = 25^{\circ}C$		1500	V	

This thyristor has been designed for use as a fluorescent tube starter switch.

An electronic starter circuit provides :

Figure 1: Basic application diagram



1/ Pre-heating

At rest the switch S is opened and when the mains voltage is applied across the circuit a full wave rectified current flows through the resistor R and the TN22 gate : at every half-cycle when this current reaches the gate triggering current (I_{GT}) the thyris tor turns on.

When the device is turned on the heating current, limited by the ballast choke, flows through the tube heaters.

The pre-heating time is typically 2 or 3 seconds.

2/ Pulsing

At the end of the pre-heating phase the switch S is turned on. At this moment :

If the current through the devices is higher than the holding current (I_H) the thyristor remains on until the current falls below I_H . Then the thyristor turns off.

If the current is equal or lower than the holding current the thyristor turns off instantaneously.

When the thyristor turns off the current flowing through the ballast choke generates a high voltage

pulse. This overvoltage is clamped by the thyristor avalanche characteristic (V_{BR}).

A pre-heating period during which a heating cur-

One or several high voltage striking pulses

rent is applied to the cathode heaters.

across the lamp.

If the lamp is not struck after the first pulse, the system starts a new ignition sequence again.

3/ Steady state

When the lamp is on the running voltage is about 150V and the starter switch is in the off-state.

IMPLEMENTATION

The resistor R must be chosen to ensure a proper triggering in the worst case (minimum operating temperature) according to the specified gate triggering current and the peak line voltage.

Switch S : This function can be realized with a gate sensitive SCR type : P0130AA 1EA3

This component is a low voltage device (< 50V) and the maximum current sunk through this switch can reach the level of the thyristor holding current. The pre-heating period can be determined by the time constant of a capacitor-resistor circuit charged by the voltage drop of diodes used in series in the thyristor cathode.

Figure 2: Maximum average power dissipation versus average on-state current (rectified full sinewave)

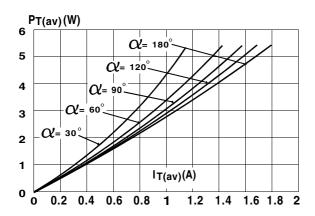


Figure 4: Averrage on-state current versus case temperature (rectified full sine wave)

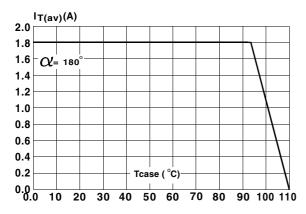


Figure 6: Relative variation of gate trigger current and holding current versus junction temperature

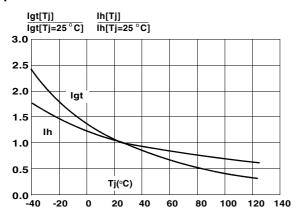


Figure 3: Correlation between maximum average power dissipation and maximum allowable temperature (T_{amb} and T_{case}) for different thermal resistances heatsink + contact

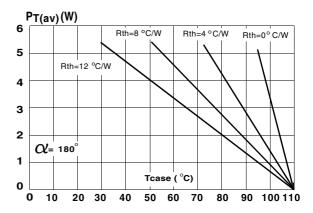


Figure 5: Thermal transient impedance junction to ambient versus pulse duration

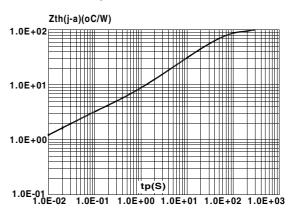
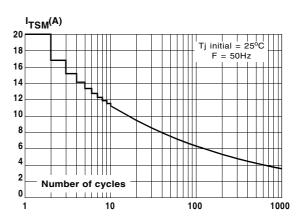


Figure 7: Non repetitive surge peak on-state current versus number of cycles



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Figure 8: Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t_p = 10ms$, and corresponding value fo l^2t

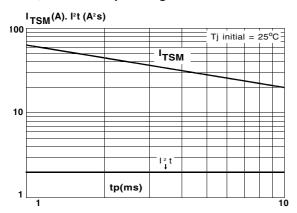
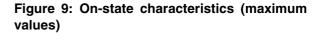


Figure 10: Relative variation of holding current versus gate-cathode resistance (typical values)



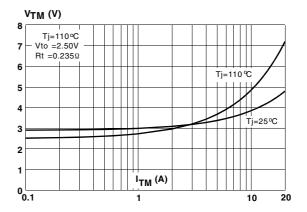
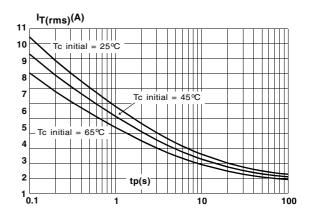
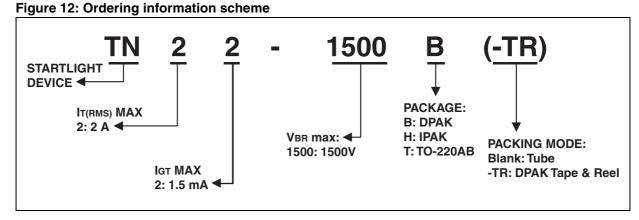


Figure 11: Maximum allowable RMS current versus time conduction and initial case temperature. Note: Calculation made fot $T_j max = 135^{\circ}C$ (the failure mode will be short circuit)





Ti=25°C

1000

 $Rgk(\Omega)$

100

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IH (mA)

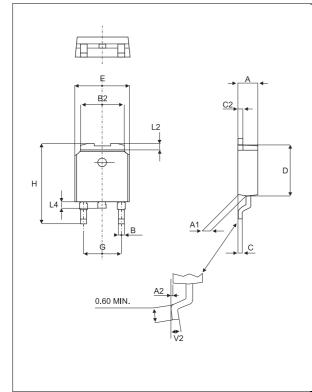
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500

100

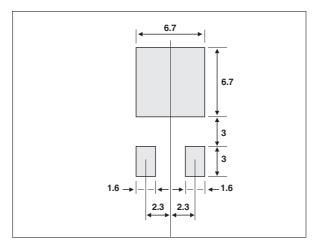
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	DIMENSIONS					
REF.	Millimeters		Inc	hes		
	Min.	Max.	Min.	Max.		
А	2.2	2.4	0.086	0.094		
A1	0.9	1.1	0.035	0.043		
A2	0.03	0.23	0.001	0.009		
В	0.64	0.9	0.025	0.035		
B2	5.2	5.4	0.204	0.212		
С	0.45	0.6	0.017	0.023		
C2	0.48	0.6	0.018	0.023		
D	6	6.2	0.236	0.244		
Е	6.4	6.6	0.251	0.259		
G	4.4	4.6	0.173	0.181		
Н	9.35	10.1	0.368	0.397		
L2	0.80	0.80 Typ.		Тур.		
L4	0.6	1.0	0.023	0.039		
V2	0°	8°	0°	8 °		

Figure 14: Footprint dimensions (in millimeters)



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Figure 15: TO-220 Package mechanical data

				DIMEN	ISIONS	
		REF.	Millin	neters	Inc	hes
			Min.	Max.	Min.	Max.
H2	A →	А	4.40	4.60	0.173	0.181
	→ C	С	1.23	1.32	0.048	0.051
		D	2.40	2.72	0.094	0.107
	+++	Е	0.49	0.70	0.019	0.027
		F	0.61	0.88	0.024	0.034
F2 F2		F1	1.14	1.71	0.044	0.066
	D ↔	F2	1.14	1.70	0.044	0.066
L4		G	4.95	5.15	0.194	0.202
F _{⊁ ←}		G1	2.40	2.70	0.094	0.106
G <u>1</u>	M ■	H2	10	10.40	0.393	0.409
G		L2	16.4	Тур.	0.645	5 Тур.
		L4	13	14	0.511	0.551
		L5	2.65	2.95	0.104	0.116
		L6	15.25	15.75	0.600	0.620
		L7	6.20	6.60	0.244	0.259
		L9	3.50	3.93	0.137	0.154
		М	2.6	Тур.	0.102	2 Typ.
		Diam	3.75	3.85	0.147	0.151

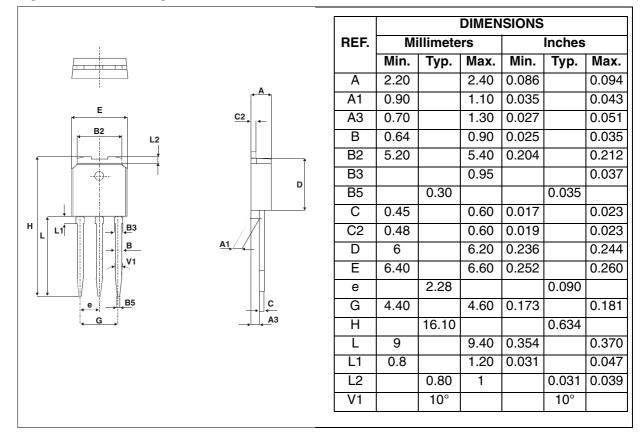


Figure 16: IPAK Package mechanical data

Table 4: Ordering information

Туре	Marking	Package	Weight	Base Qty	Delivery mode
TN22-1500B	TN22-1500	DPAK	0.3 g	75	Tube
TN22-1500B-TR	TN22-1500	DPAK	0.3 g	2500	Tape & Reel
TN22-1500H	TN22-1500	IPAK	0.4 g	75	Tube
TN22-1500T	TN22-1500	TO-220AB	2.0 g	50	Tube

Table 5: Revision History

Date	Revision	Description of Changes
Oct-2000	1	First issue.
17-Sep-2005	2	TO-220AB package added.

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